

Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	- 250	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10\text{ V}$	1.0
Q_g (Max.) (nC)	38	
Q_{gs} (nC)	8.0	
Q_{gd} (nC)	18	
Configuration	Single	

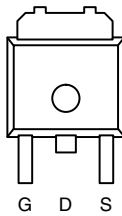
FEATURES

- Advanced Process Technology
- Dynamic dV/dt Rating
- 150 °C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated
- Lead (Pb)-free Available



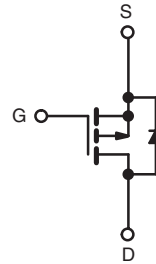
RoHS*
COMPLIANT

TO-252



Top View

Drain Connected to Tab



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	- 250	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at - 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	- 6.0	A
		$T_C = 100\text{ }^{\circ}\text{C}$		- 4.0	
Pulsed Drain Current ^a			I_{DM}	- 16	
Linear Derating Factor				0.28	W/ $^{\circ}\text{C}$
Single Pulse Avalanche Energy ^b			E_{AS}	520	mJ
Repetitive Avalanche Current ^a			I_{AR}	- 4.1	A
Repetitive Avalanche Energy ^a			E_{AR}	3.5	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$		P_D	85	W
Peak Diode Recovery dV/dt ^c			dV/dt	- 5.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Soldering Recommendations (Peak Temperature)		for 10 s		300 ^d	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 62\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AS} = -4.1\text{ A}$ (see fig. 12).
- $I_{SD} \leq -4.1\text{ A}$, $dI/dt \leq -640\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^{\circ}\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.6	

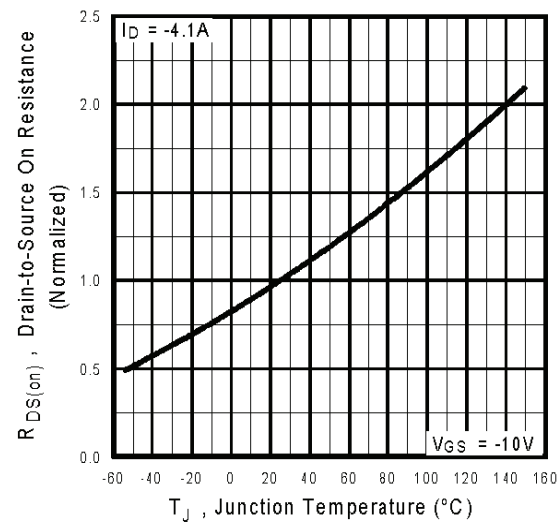
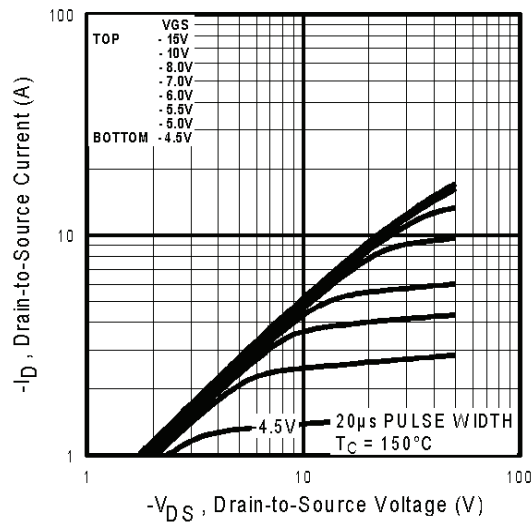
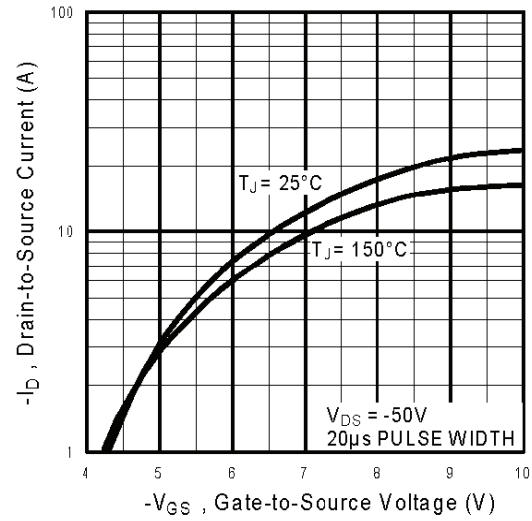
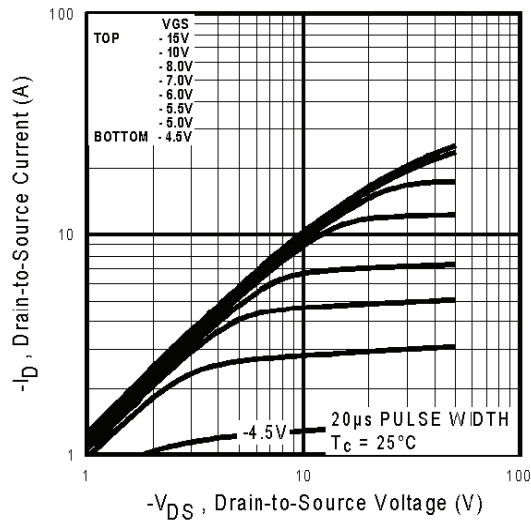
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

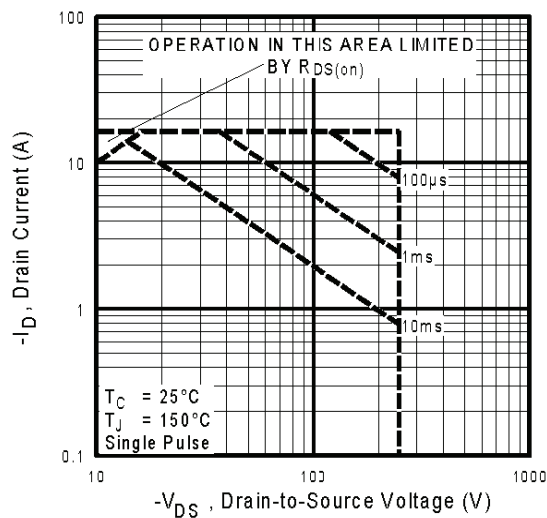
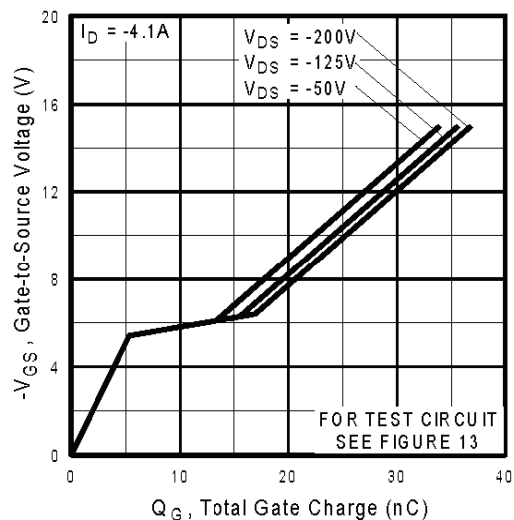
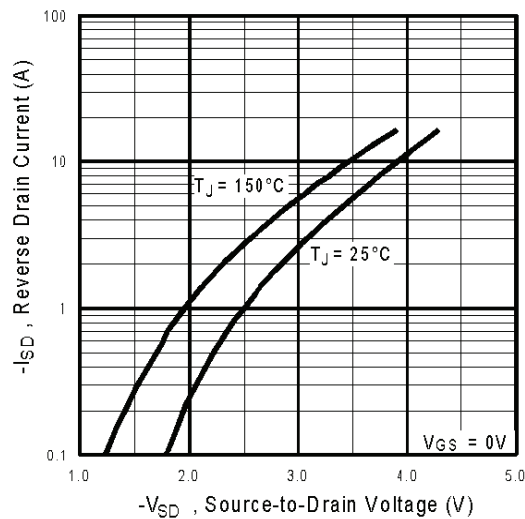
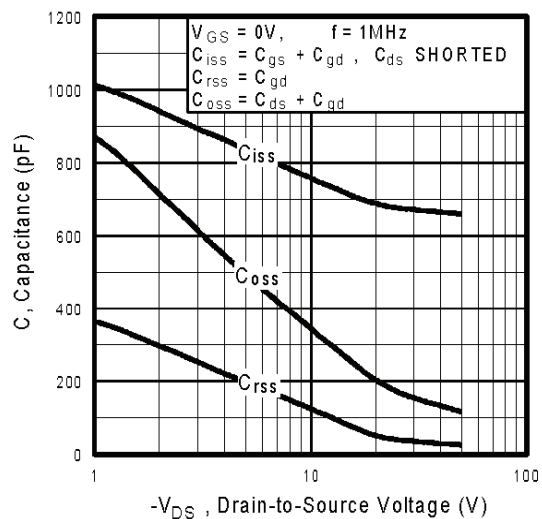
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		- 250	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	- 0.27	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		- 2.0	-	- 4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 250 V, V _{GS} = 0 V		-	-	- 25	μA
		V _{DS} = - 200 V, V _{GS} = 0 V, T _J = 150 °C		-	-	- 250	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 2.5 A ^b	-	1.0	-	Ω
Forward Transconductance	g _{fs}	V _{DS} = - 50 V, I _D = - 4.1 A ^b		2.2	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1.0 MHz, see fig. 5		-	680	-	pF
Output Capacitance	C _{oss}			-	170	-	
Reverse Transfer Capacitance	C _{rss}			-	40	-	
Drain to Sink Capacitance	C	f = 1.0 MHz		-	12	-	
Total Gate Charge	Q _g	V _{GS} = - 10 V	I _D = - 4.1 A, V _{DS} = - 200 V, see fig. 6 and 13 ^b	-	-	38	nC
Gate-Source Charge	Q _{gs}			-	-	8.0	
Gate-Drain Charge	Q _{gd}			-	-	18	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 130 V, I _D = - 4.1 A, R _G = 12 Ω, R _D = 31 Ω, see fig. 10 ^b		-	12	-	ns
Rise Time	t _r			-	23	-	
Turn-Off Delay Time	t _{d(off)}			-	34	-	
Fall Time	t _f			-	21	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L _S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	- 4.1	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	- 16	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = - 4.1 A, V _{GS} = 0 V ^b		-	-	- 6.5	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = - 4.1 A, dI/dt = -100 A/μs ^b		-	190	290	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	1.5	2.2	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





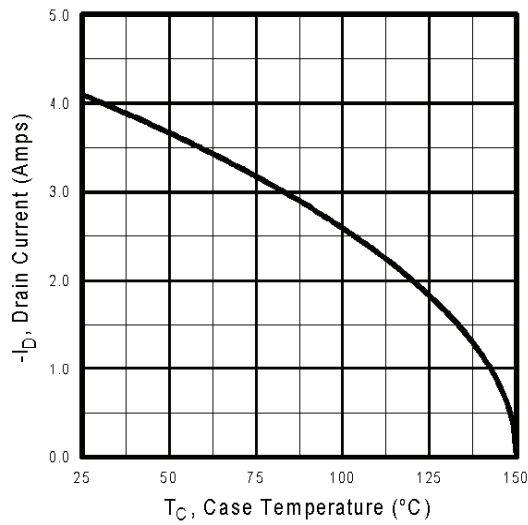


Fig. 9 - Maximum Drain Current vs. Case Temperature

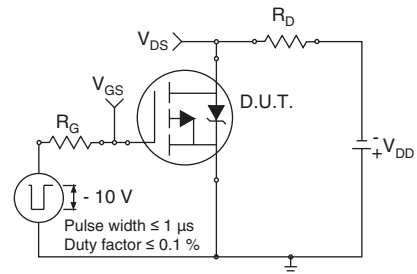


Fig. 10a - Switching Time Test Circuit

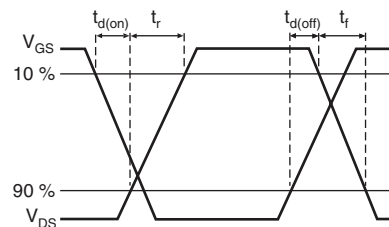


Fig. 10b - Switching Time Waveforms

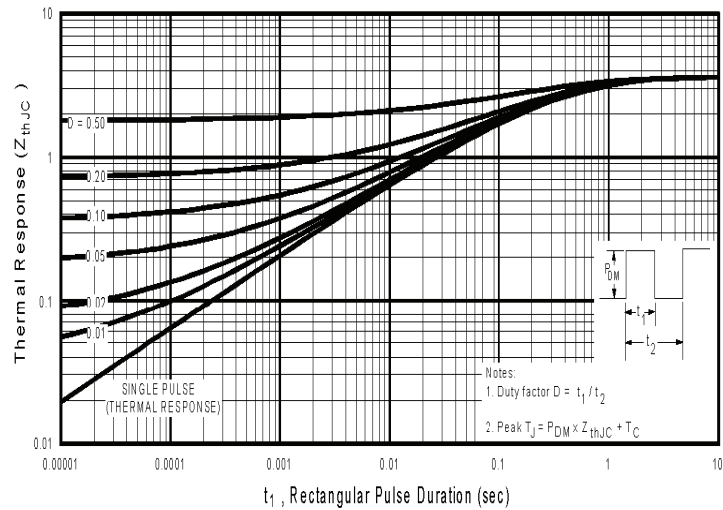


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

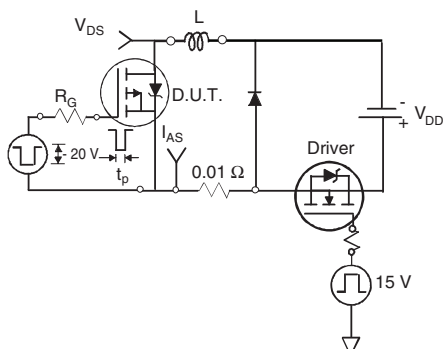


Fig. 12a - Unclamped Inductive Test Circuit

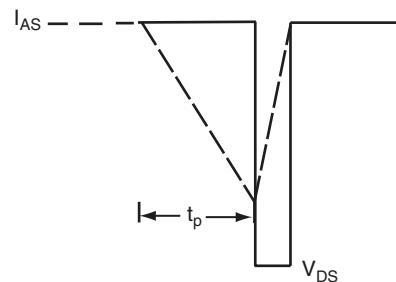


Fig. 12b - Unclamped Inductive Waveforms

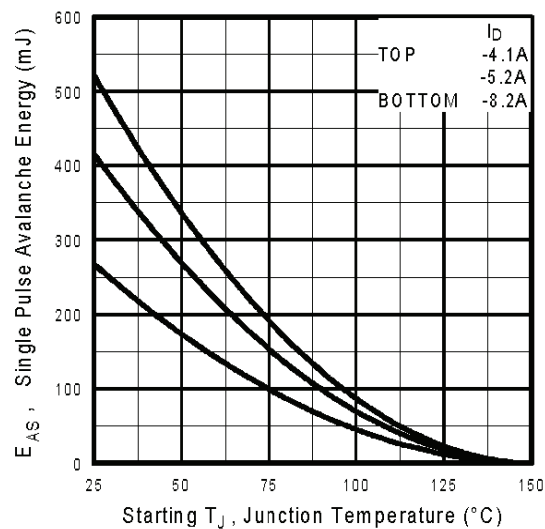


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

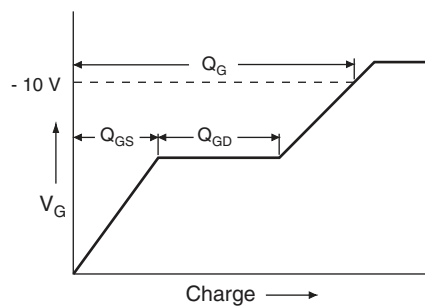


Fig. 13a - Basic Gate Charge Waveform

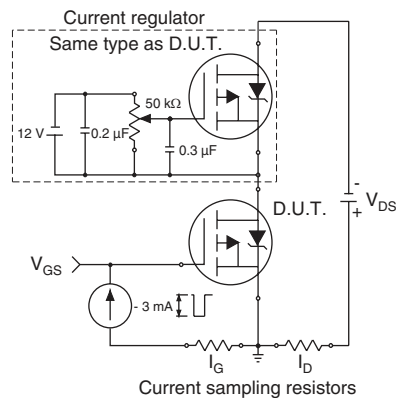
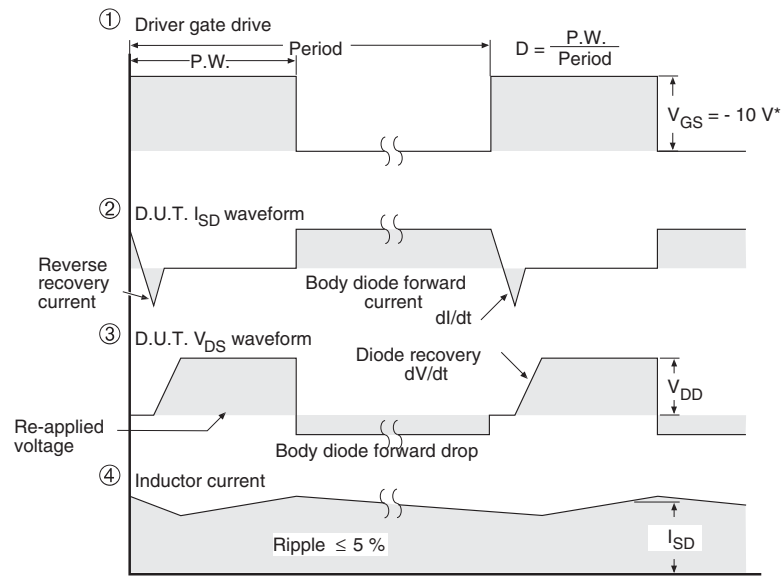
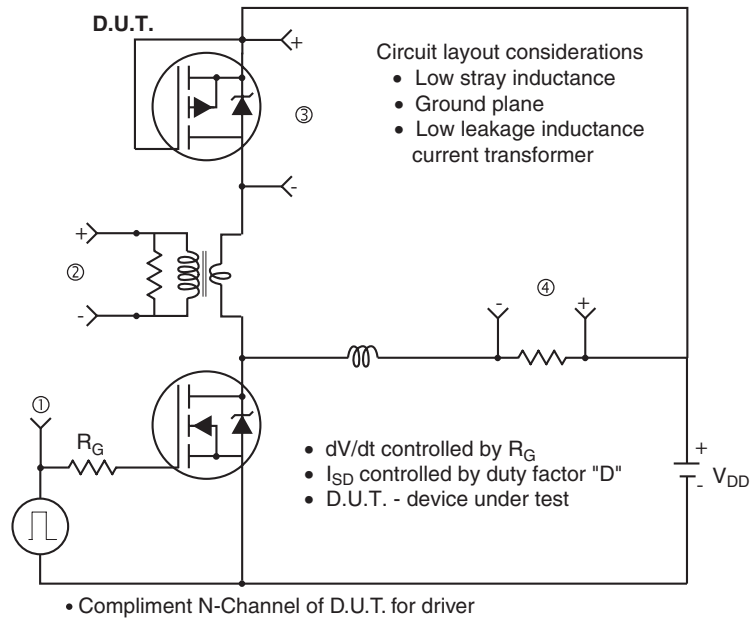


Fig. 13b - Gate Charge Test Circuit

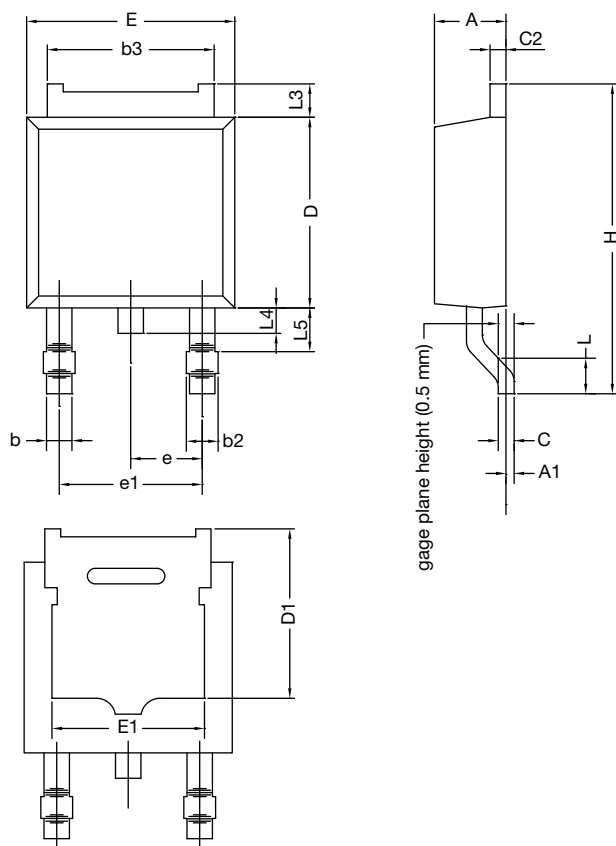
Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = -5 V$ for logic level and $-3 V$ drive devices

Fig. 14 - For P-Channel

TO-252AA CASE OUTLINE

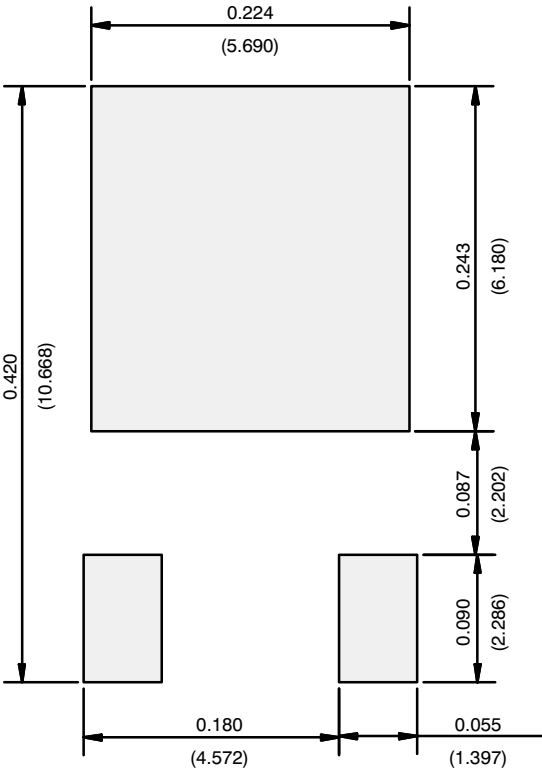


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12				
DWG: 5347				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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